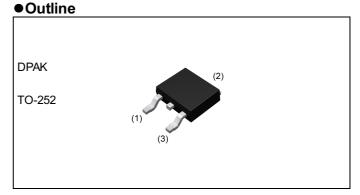
Pch -60V -29A Power MOSFET

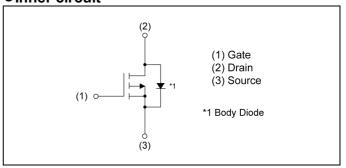
V <sub>DSS</sub>	-60V
R <sub>DS(on)</sub> (Max.)	55mΩ
I <sub>D</sub>	±29A
P <sub>D</sub>	53W



## Features

Low on-resistance Pd-free plating;RoHS compliant 100% Avalanche tested AEC-Q101 qualified

## •Inner circuit



## Application

ADAS/Info./Lighting/Body

## Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	330
Туре	Tape width (mm)	16
	Quantity (pcs)	2500
	Taping code	TL
	Marking	RD3L03BBJ

## ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source voltage		$V_{\rm DSS}$	-60	V
Continuous drain current	V <sub>GS</sub> = -10V	I <sub>D</sub> *1	±29	Α
Pulsed drain current	l <sub>DP</sub> *2	±58	Α	
Gate - Source voltage		V <sub>GSS</sub>	+5/-20	V
Avalanche current, single pulse	I <sub>AS</sub> *3	-20.0	Α	
Avalanche energy, single pulse	E <sub>AS</sub> *3	14.8	mJ	
Power dissipation		P <sub>D</sub> *1	53	W
Junction temperature	T <sub>j</sub>	175	°C	
Operating junction and storage te	mperature range	T <sub>stg</sub>	-55 to +175	°C

## ●Thermal resistance

Parameter	Symbol	Values			Lloit
		Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub> *1	-	-	2.80	°C/W

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Darameter	Symbol	Conditions	Values			- Unit	
Parameter	Parameter Symbol Conditions		Min.	Тур.	Max.	Uriil	
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V$ , $I_D = -1mA$	-60	-	-	V	
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	$\frac{\Delta V_{(BR)DSS}}{\Delta T_i} I_D = -1 \text{mA}$ referenced to 25°C		-50	-	mV/°C	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = -48V, V_{GS} = 0V$	-	-	-1	μА	
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = +5/-20V, V_{DS} = 0V$	-	-	±500	nA	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -470 \mu A$	-1.0	-	-2.5	V	
Gate threshold voltage temperature coefficient	$\frac{\DeltaV_{GS(th)}}{\DeltaT_j}$	$I_D = -470 \mu A$ referenced to 25°C	-	3.7	-	mV/°C	
Static drain - source	D *4	V <sub>GS</sub> = -10V, I <sub>D</sub> = -10A	-	43	55	m0	
on - state resistance	R <sub>DS(on)</sub> *4	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A	-	48	62	mΩ	
Gate resistance	$R_G$	f = 1MHz, open drain	-	14	-	Ω	
Forward Transfer Admittance	Y <sub>fs</sub>  *4	V <sub>DS</sub> = -5V, I <sub>D</sub> = -10A	11	-	-	S	

<sup>\*1</sup>  $T_c$ =25°C , Limited only by maximum junction temperature  $T_i$ =175°C.

<sup>\*2</sup> Pw ≤10µs , Duty cycle ≤1%

<sup>\*3</sup> L=0.05mH,  $V_{DD}$ =-30V,  $R_G$ =25 $\Omega$ , Starting  $T_i$ =25 $^{\circ}$ C, See Fig.3-1,3-2

<sup>\*4</sup> Pulsed

# • Electrical characteristics $(T_a = 25^{\circ}C)$

Davanastan	Cumbal	Conditions	Values			Unit	
Parameter	Symbol Conditions		Min.	Тур.	Max.	UIIIL	
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	1400	-		
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -30V	-	115	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	85	-		
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} \simeq -30V, V_{GS} = -10V$	1	10	1		
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = -10A	1	15	1	no	
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L \simeq 3\Omega$	-	93	-	ns	
Fall time	t <sub>f</sub> *4	$R_G = 1\Omega$	-	25	-		

# ● Gate charge characteristics (T<sub>a</sub> = 25°C)

Davanatar	Currente e l	Conditions			Values		l lait
Parameter	Symbol			Min.	Тур.	Max.	Unit
Total gate charge	O *4		V <sub>GS</sub> = -10V	-	27.0	-	
Total gate charge	Q <sub>g</sub> *4	V <sub>DD</sub> ≃ <b>-</b> 30V		-	12.1	-	»C
Gate - Source charge	Q <sub>gs</sub> *4	I <sub>D</sub> = -10A	V <sub>GS</sub> = -4.5V	-	3.2	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4			-	4.0	-	

# ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Cumbal	Conditions	Values			Unit
raiametei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous forward current	I <sub>S</sub> *1	T = 25°C	-	-	-29	Α
Pulse forward current	I <sub>SP</sub> *2	T <sub>a</sub> = 25°C	-	-	-58	Α
Forward voltage	V <sub>SD</sub> *4	$V_{GS} = 0V, I_S = -29A$	-	-	-1.2	V
Reverse recovery time	t <sub>rr</sub> *4	I <sub>S</sub> = -10A, V <sub>GS</sub> =0V	-	25	-	ns
Reverse recovery charge	Q <sub>rr</sub> *4	di/dt = -100A/µs	-	23	-	nC

Power Dissipation: P<sub>D</sub>/P<sub>Dmax</sub>. [%]

## • Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

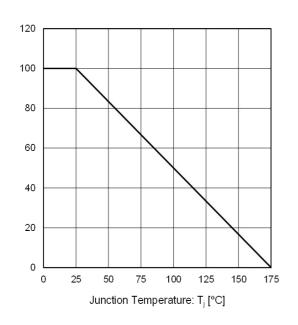
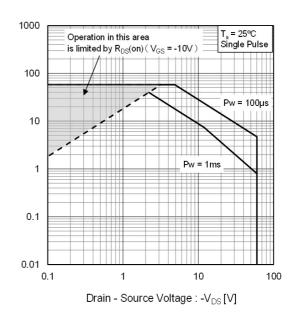


Fig.2 Maximum Safe Operating Area



Drain Current : -I<sub>D</sub> [A]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

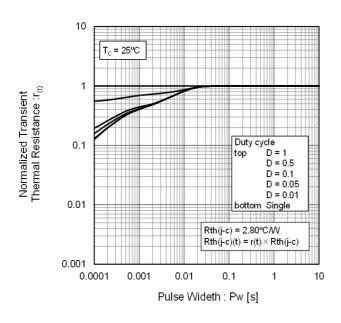
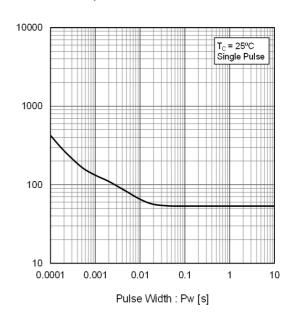
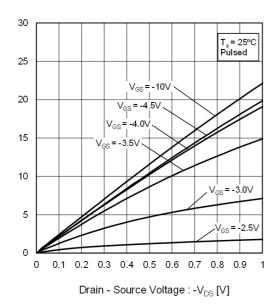


Fig.4 Single Pulse Maximum Power dissipation



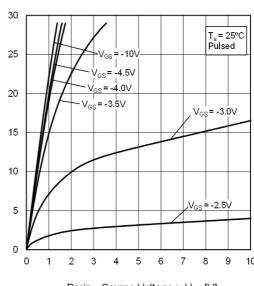
Peak Transient Power: P[W]

Fig.5 Typical Output Characteristics(I)



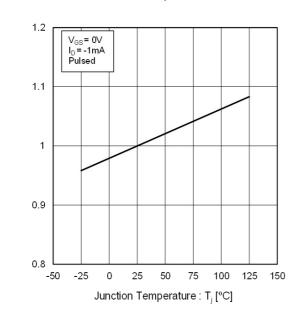
Drain Current: -I<sub>D</sub> [A]

Fig.6 Typical Output Characteristics(II)



Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.7 Normalized Breakdown Voltage vs. Junction Temperature



Drain Current : -I<sub>D</sub> [A]

Fig.8 Typical Transfer Characteristics

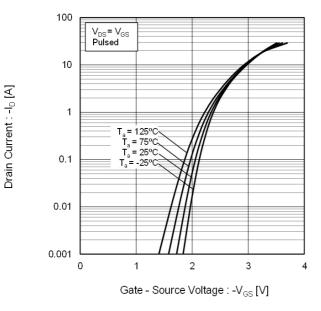


Fig.9 Gate Threshold Voltage vs.
Junction Temperature

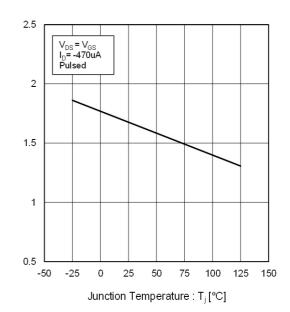
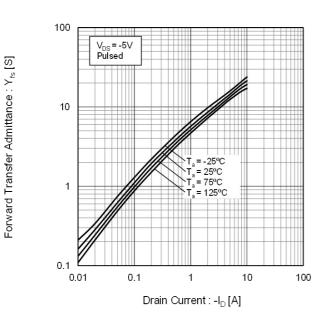


Fig.10 Forward Transfer Admittance vs.
Drain Current



Gate Threshold Voltage : - $V_{GS(th)}[V]$ 

Fig.11 Drain Current Derating Curve

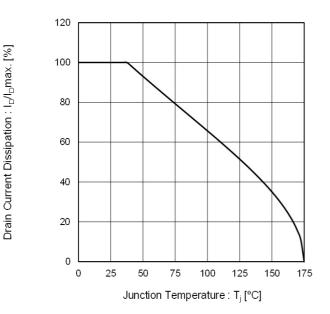
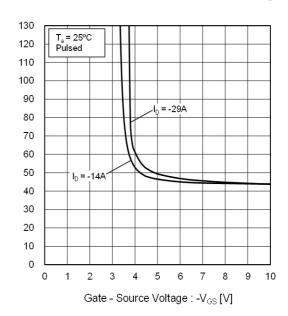


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Static Drain - Source On-State Resistance :  $R_{\text{DS}(on)}\left[\text{m}\Omega\right]$ 

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

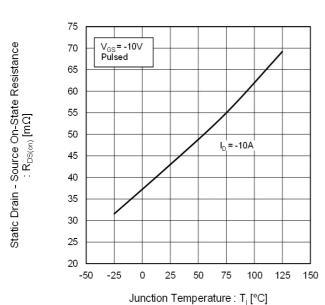


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (I)

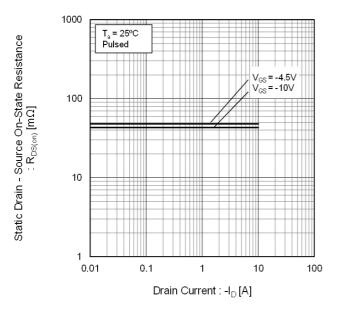


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

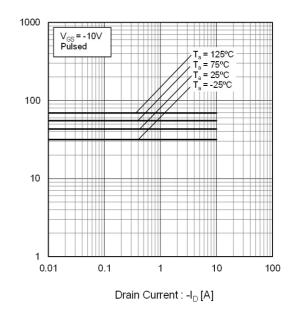
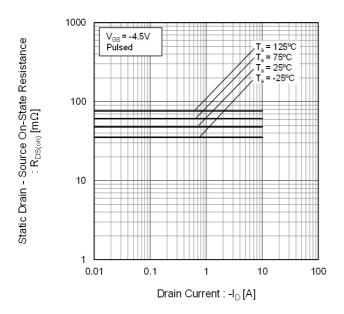


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (III)



Static Drain - Source On-State Resistance :  $R_{DS(\sigma n)} \left[ m \Omega \right]$ 

Fig.17 Typical Capacitance vs.

Drain - Source Voltage

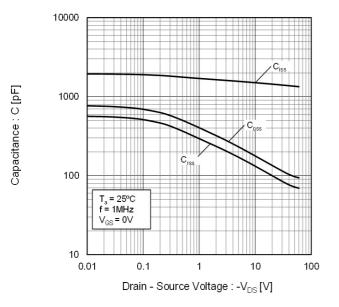


Fig.18 Switching Characteristics

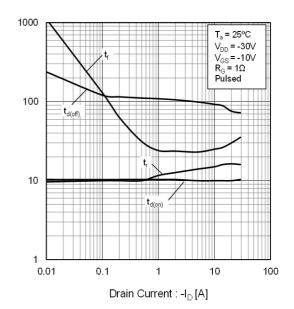


Fig.19 Dynamic Input Characteristics

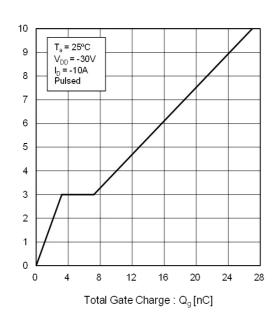
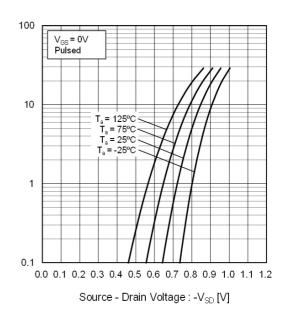


Fig.20 Source Current vs.

Source Drain Voltage



Gate - Source Voltage : - $V_{GS}$  [V]

Source Current : -I<sub>s</sub> [A]

Switching Time : t [ns]

## Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

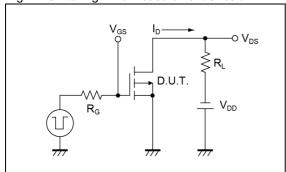


Fig.2-1 Gate Charge Measurement Circuit

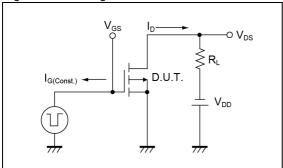


Fig.3-1 Avalanche Measurement Circuit

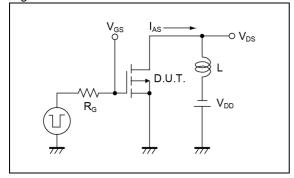


Fig.1-2 Switching Waveforms

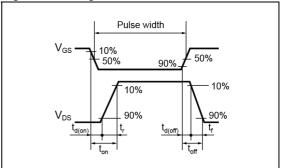


Fig.2-2 Gate Charge Waveform

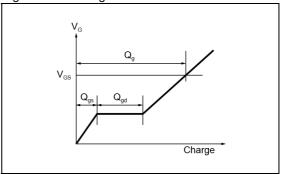
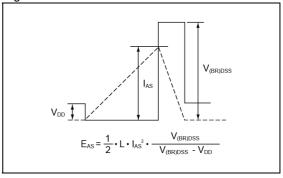
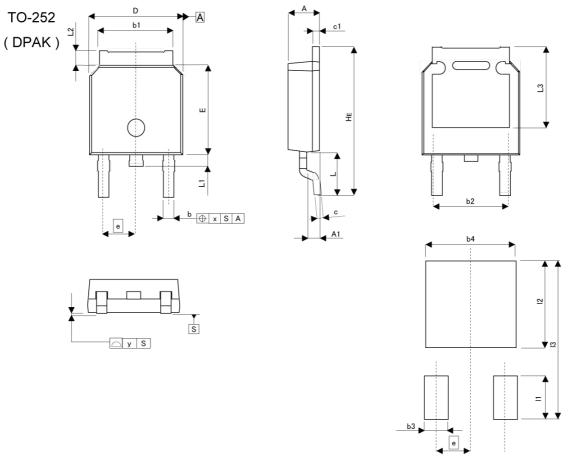


Fig.3-2 Avalanche Waveform



## Dimensions



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIME	TERS	INCI	HES
DIIVI	MIN	MAX	MIN	MAX
Α	2.10	2.30	0.083	0.091
A1	0.70	1.10	0.028	0.043
b	0.65	0.85	0.026	0.033
b1	5.10	5.40	0.201	0.213
b2	5.	10	0.2	201
С	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.40	6.80	0.252	0.268
е	2.	30	0.0	91
Е	6.00	6.40	0.236	0.252
HE	9.50	10.50	0.374	0.413
L	2.	90	0.1	14
L1	0.70	0.90	0.028	0.035
L2	0.70	1.30	0.028	0.051
L3	5.	5.30		209
Х	-	0.25	-	0.010
у	-	0.10	-	0.004

DIM	MILIME	TERS	INCHES		
DIIVI	MIN	MAX	MIN	MAX	
b3	o <del>-</del>	1.10	-	0.043	
b4	1-	5.40	-	0.213	
l1	-	2.90	1	0.114	
12	-	5.50	-	0.217	
13	_	10.50	_	0.413	

Dimension in mm/inches



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1. If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

ſ	JÁPAN	USA	EU	CHINA
Ī	CLASSⅢ	CL ACCIII	CLASS II b	СГУССШ
ſ	CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
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  - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
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  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### **Precautions Regarding Application Examples and External Circuits**

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

#### **Precaution for Product Label**

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

#### **Precaution for Disposition**

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